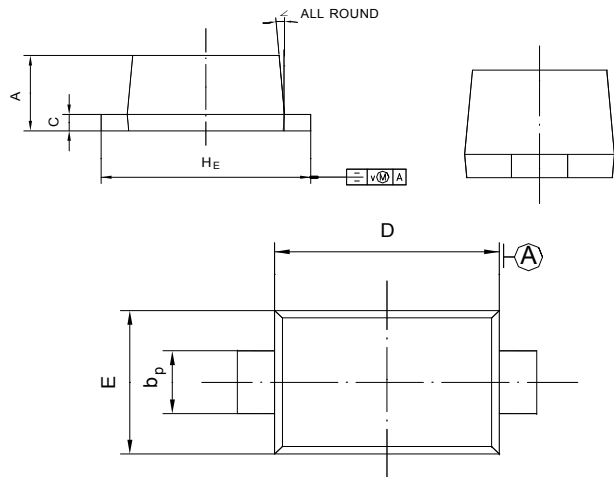


Schottky Barrier Diode

FEATURES

- Small surface mounting type
- Low I_R
- High reliability



UNIT	A	b _p	C	D	E	H _E	V	∠
mm	0.70 0.50	0.40 0.20	0.14 0.05	1.30 1.10	0.90 0.75	1.70 1.50	0.1	5°

Maximum Ratings and Electrical Characteristics, Single Diode @T_A=25°C

Parameter	Symbol	Limit	Unit
DC reverse voltage	V _R	40	V
Mean rectifying current	I _o	0.2	A
Non-repetitive peak forward surge current@t=8.3ms	I _{FSM}	1	A
Power Dissipation	P _D	150	mW
Thermal resistance from junction to ambient	R _{θJA}	667	°C/W
Junction temperature	T _J	125	°C
Storage temperature	T _{STG}	-55~+150	

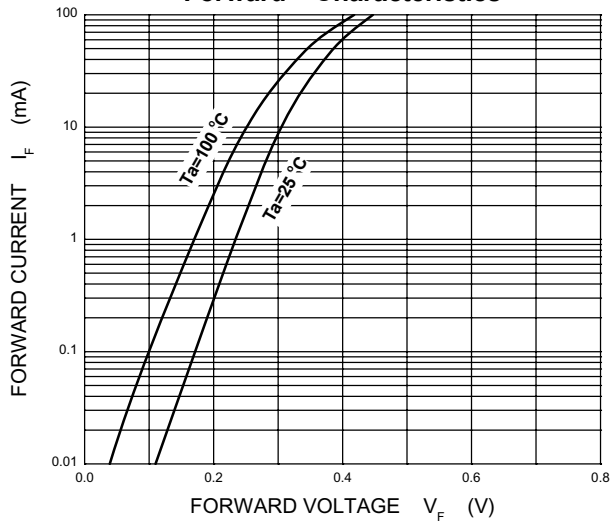
RB520S-40

Electrical Ratings @T_A=25°C

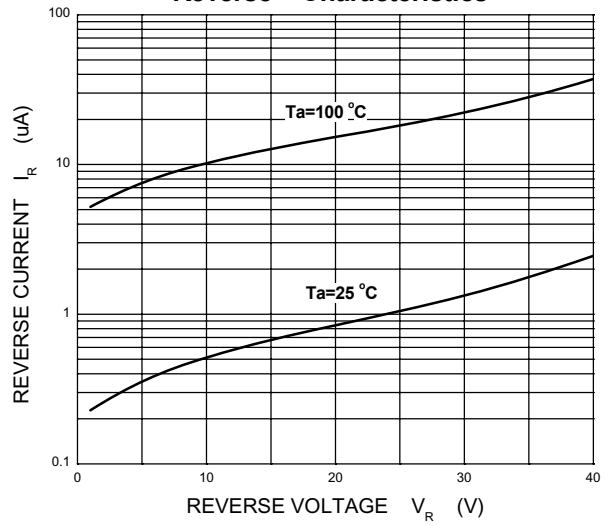
Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Forward voltage	V _F		0.304	0.39	V	I _F =10mA
			0.446	0.55		I _F =100mA
Reverse current	I _R		0.605	1	μA	V _R =10V
			2.837	10		V _R =40V

RATING AND CHARACTERISTIC CURVES (RB520S-40)

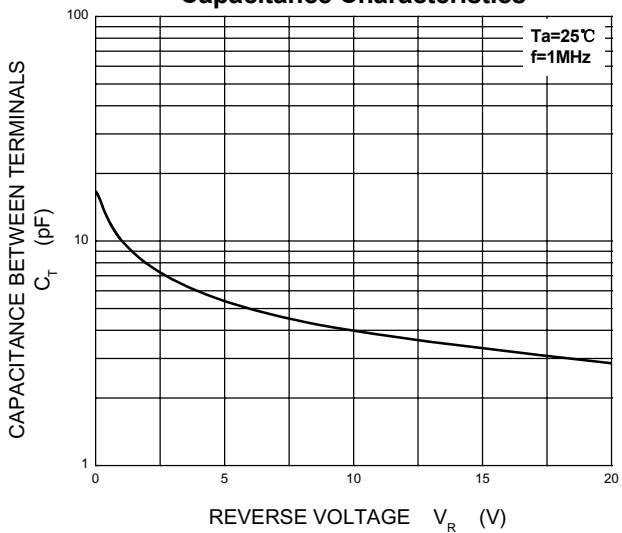
Forward Characteristics



Reverse Characteristics



Capacitance Characteristics



Power Derating Curve

